

**DISCONTINUED**  
**PLEASE USE ZTX601**

# NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

## FXT601B

**ISSUE 1 – MARCH 94**

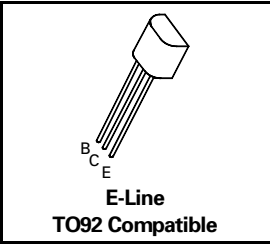
**FEATURES**

- \* 160 Volt  $V_{CEO}$
- \* Gain of 5K at  $I_C=1$  Amp
- \*  $P_{tot} = 1$  Watt

**APPLICATIONS**

- \* Lamp, solenoid and relay drivers
- \* Replacement of TO126 and TO220 packages

REFER TO ZTX601B FOR GRAPHS



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Peak Pulse Current	$I_{CM}$	4	A
Continuous Collector Current	$I_C$	1	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^\circ\text{C}$  unless otherwise stated).**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180			V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160			V	$I_C=10\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=100\mu\text{A}, I_C=0$
Collector Cut-Off Current	$I_{CBO}$			0.01 10	$\mu\text{A}$ $\mu\text{A}$	$V_{CB}=160\text{V}$ $V_{CB}=160\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$			0.1	$\mu\text{A}$	$V_{EB}=8\text{V}, I_C=0$
Collector-Emitter Cut-Off Current	$I_{CES}$			10	$\mu\text{A}$	$V_{CES}=160\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.75 0.85	1.1 1.2	V V	$I_C=0.5\text{A}, I_B=5\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.7	1.9	V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.5	1.7	V	$I_C=1\text{A}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	5K 10K 5K	10K 20K 10K	100K		$I_C=50\text{mA}, V_{CE}=10\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=10\text{V}^*$ $I_C=1\text{A}, V_{CE}=10\text{V}^*$
Transition Frequency	$f_T$	150	250		MHz	$I_C=100\text{mA}, V_{CE}=10\text{V}$ $f=20\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$